

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(cleaning and substrate and (insulator or dielectric or oxide) and (high\$k with dielectric) and (hydrogen with anneal) and (oxygen with anneal)).CLM.	US-PGPUB	OR	ON	2005/11/17 16:10
L2	3	(substrate and (chamber or reactor) and ((loading or (heat with gas)) with treatment) and poly\$silicon). clm.	US-PGPUB	OR	ON	2005/11/17 16:18
L3	1	(substrate and (insulator or dielectric or oxide) and high\$k and anneal\$3 and ((loading or (heat with gas)) with treatment) and poly\$silicon).clm.	US-PGPUB	OR	ON	2005/11/17 16:19